

MOSFET

600V CoolMOS™ G7 SJ Power Device

The C7 GOLD series (G7) for the first time brings together the benefits of the C7 GOLD CoolMOS™ technology, 4 pin Kelvin Source capability and the improved thermal properties of the TOLL package to enable a possible SMD solution for high current topologies such as PFC up to 3kW

Features

- C7 Gold gives best in class FOM $R_{DS(on)} \cdot E_{oss}$ and $R_{DS(on)} \cdot Q_g$.
- Suitable for hard and soft switching (PFC and high performance LLC)
- C7 Gold technology enables best in class $R_{DS(on)}$ in smallest footprint.
- TOLL package has inbuilt 4th pin Kelvin Source configuration and low parasitic source inductance ($\sim 1nH$).
- TOLL package is MSL1 compliant, total Pb-free and has easy visual inspection grooved leads.
- TOLL SMD package combined with lead free die attach process enables improved thermal performance R_{th} .

Benefits

- C7 Gold FOM $R_{DS(on)} \cdot Q_g$ is 15% better than previous C7 600V enabling faster switching leading to higher efficiency.
- Increased economies of scale by use in PFC and PWM topologies in the application
- C7 Gold can reach 28mΩ in in TOLL 115mm² footprint, whereas previous BIC C7 600V was 40mΩ in 150mm² D²PAK footprint.
- Reducing parasitic source inductance by Kelvin Source improves efficiency by faster switching and ease of use due to less ringing.
- TOLL package is easy to use and has the highest quality standards.
- Improved thermals enable SMD TOLL package to be used in higher current designs than has been previously possible.

Potential applications

PFC stages and PWM stages (TTF, LLC) for high power/performance SMPS e.g. Computing, Server, Telecom, UPS and Solar.

Product validation

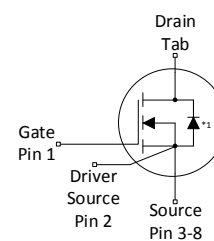
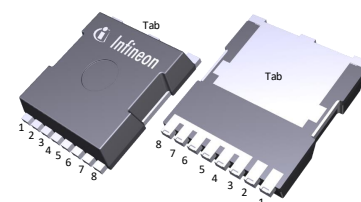
Fully qualified according to JEDEC for Industrial Applications

Please note: For MOSFET paralleling the use of ferrite beads on the gate or separate totem poles is generally recommended.

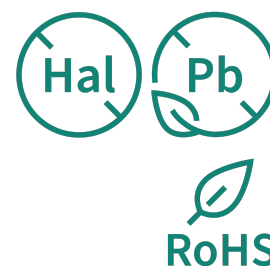
Table 1 Key performance parameters

Parameter	Value	Unit
$V_{DS} @ T_{j,max}$	650	V
$R_{DS(on),max}$	102	mΩ
$Q_{g,typ}$	34	nC
$I_{D,pulse}$	66	A
$I_{D,continuous} @ T_j < 150^\circ C$	32	A
$E_{oss}@400V$	4	μJ
Body diode di/dt	740	A/μs

TOLL



*1: Internal body diode



Part number	Package	Marking	Related links
IPT60R102G7	PG-HSOF-8	60R102G7	see Appendix A



Table of contents

Description 1

Maximum ratings 3

Thermal characteristics 4

Electrical characteristics 5

Electrical characteristics diagrams 7

Test circuits 11

Package outlines 12

Appendix A 15

Revision history 16

Trademarks 17

Disclaimer 17

1 Maximum ratings

at $T_j = 25^\circ\text{C}$, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Continuous drain current ¹⁾	I_D	-	-	23	A	$T_C = 25^\circ\text{C}$
				15		$T_C = 100^\circ\text{C}$
Pulsed drain current ²⁾	$I_{D,pulse}$	-	-	66	A	$T_C = 25^\circ\text{C}$
Avalanche energy, single pulse	E_{AS}	-	-	78	mJ	$I_D = 4.4\text{A}$; $V_{DD} = 50\text{V}$; see table 10
Avalanche energy, repetitive	E_{AR}			0.39		
Avalanche current, single pulse	I_{AS}	-	-	4.4	A	-
MOSFET dv/dt ruggedness	dv/dt	-	-	120	V/ns	$V_{DS} = 0 \dots 400\text{V}$
Gate source voltage (static)	V_{GS}	-20	-	20	V	static;
Gate source voltage (dynamic)	V_{GS}	-30	-	30	V	AC ($f > 1\text{ Hz}$)
Power dissipation	P_{tot}	-	-	141	W	$T_C = 25^\circ\text{C}$
Storage temperature	T_{stg}	-55	-	150	$^\circ\text{C}$	-
Operating junction temperature	T_j	-55		150	$^\circ\text{C}$	
Mounting torque	-	-		n.a.	Ncm	
Continuous diode forward current	I_S	-	-	23	A	$T_C = 25^\circ\text{C}$
Diode pulse current ²⁾	$I_{S,pulse}$			66		
Reverse diode dv/dt ³⁾	dv/dt	-	-	25	V/ns	$V_{DS} = 0 \dots 400\text{V}$, $I_{SD} \leq 6.7\text{A}$, $T_j = 25^\circ\text{C}$ see table 8
Maximum diode commutation speed	di _t /dt			740	A/ μs	
Insulation withstand voltage	V_{ISO}	-	-	n.a.	V	V_{rms} , $T_C = 25^\circ\text{C}$, $t = 1\text{min}$

1) Limited by $T_{j,max}$.

2) Pulse width t_p limited by $T_{j,max}$

3) Identical low side and high side switch

2 Thermal characteristics

Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	R_{thJC}	-	-	0.888	°C/W	-
Thermal resistance, junction - ambient	R_{thJA}	-	-	62	°C/W	device on PCB, minimal footprint
Thermal resistance, junction - ambient for SMD version	R_{thJA}	-	35	45	°C/W	Device on 40mm*40mm*1.5mm epoxy PCB FR4 with 6cm ² (one layer, 70µm thickness) copper area for drain connection and cooling. PCB is vertical without air stream cooling.
Soldering temperature, wave- & reflow soldering allowed	T_{sold}	-	-	260	°C	reflow MSL1

3 Electrical characteristics

at $T_j=25^\circ\text{C}$, unless otherwise specified

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	600	-	-	V	$V_{GS}=0V, I_D=1mA$
Gate threshold voltage	$V_{(GS)th}$	3	3.5	4	V	$V_{DS}=V_{GS}, I_D=0.39mA$
Zero gate voltage drain current	I_{DSS}	-	-	1	μA	$V_{DS}=600, V_{GS}=0V, T_j=25^\circ\text{C}$
			10	-		$V_{DS}=600, V_{GS}=0V, T_j=150^\circ\text{C}$
Gate-source leakage current	I_{GSS}	-	-	100	nA	$V_{GS}=20V, V_{DS}=0V$
Drain-source on-state resistance	$R_{DS(on)}$	-	0.088	0.102	Ω	$V_{GS}=10V, I_D=7.8A, T_j=25^\circ\text{C}$
			0.220	-		$V_{GS}=10V, I_D=7.8A, T_j=150^\circ\text{C}$
Gate resistance	R_G	-	0.8	-	Ω	$f=1MHz$, open drain

Table 5 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Input capacitance	C_{iss}	-	1320	-	pF	$V_{GS}=0V, V_{DS}=400V, f=250kHz$
Output capacitance	C_{oss}		27			
Effective output capacitance, energy related ⁴⁾	$C_{o(er)}$	-	50	-	pF	$V_{GS}=0V, V_{DS}=0...400V$
Effective output capacitance, time related ⁵⁾	$C_{o(tr)}$	-	516	-	pF	$I_D=\text{constant}, V_{GS}=0V, V_{DS}=0...400V$
Turn-on delay time	$t_{d(on)}$	-	18	-	ns	$V_{DD}=400V, V_{GS}=13V, I_D=7.8A, R_G=5.3\Omega$; see table 9
Rise time	t_r		5			
Turn-off delay time	$t_{d(off)}$		60			
Fall time	t_f		4			

⁴⁾ $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 400V

⁵⁾ $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 400V

Table 6 Gate charge characteristics

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{gs}	-	7	-	nC	$V_{DD}=400V, I_D=7.8A, V_{GS}=0 \text{ to } 10V$
Gate to drain charge	Q_{gd}		12		nC	
Gate charge total	Q_g		34		nC	
Gate plateau voltage	$V_{plateau}$		5.0		V	

Table 7 Reverse diode characteristics

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Diode forward voltage	V_{SD}	-	0.8	-	V	$V_{GS}=0V, I_F=7.8A, T_j=25^\circ C$
Reverse recovery time	t_{rr}	-	305	-	ns	$V_R=400V, I_F=7.8A, di_F/dt=100A/\mu s$; see table 8
Reverse recovery charge	Q_{rr}		3.1		μC	
Peak reverse recovery current	I_{rrm}		22		A	

4 Electrical characteristics diagrams

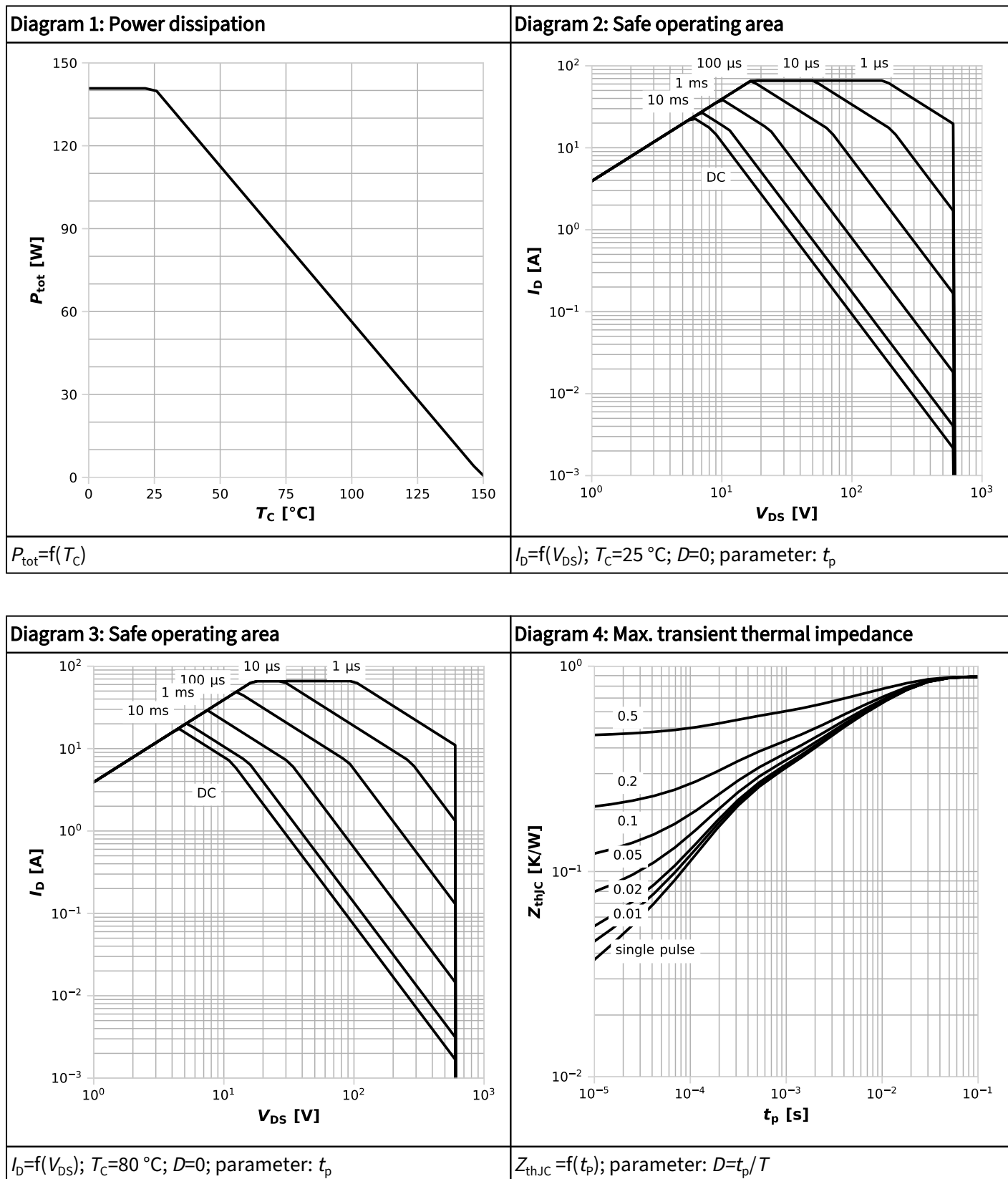
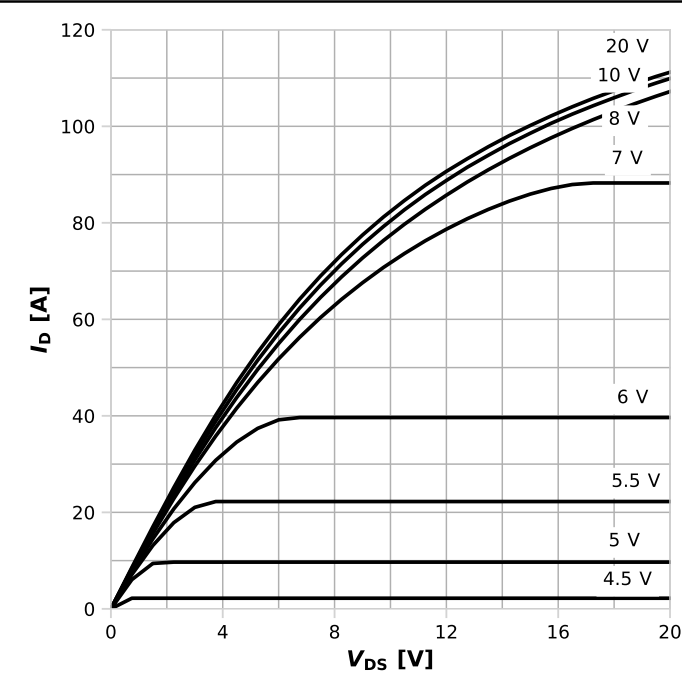
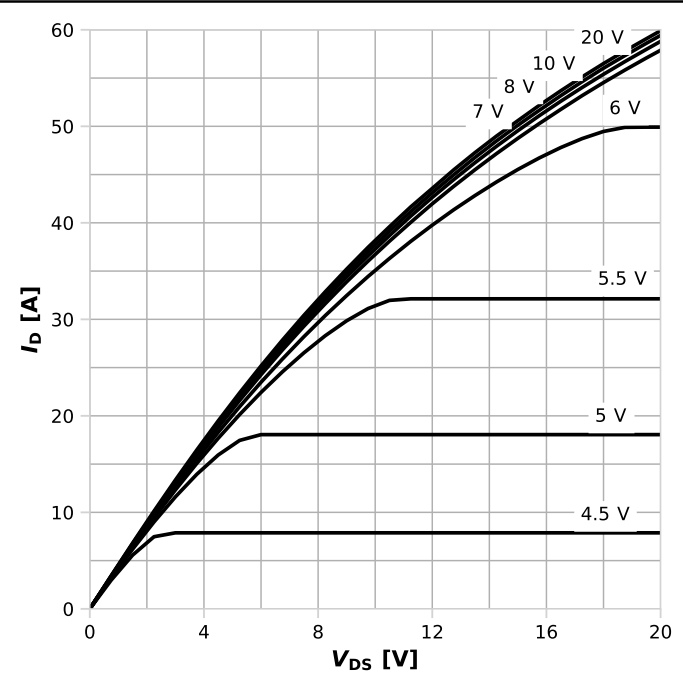


Diagram 5: Typ. output characteristics



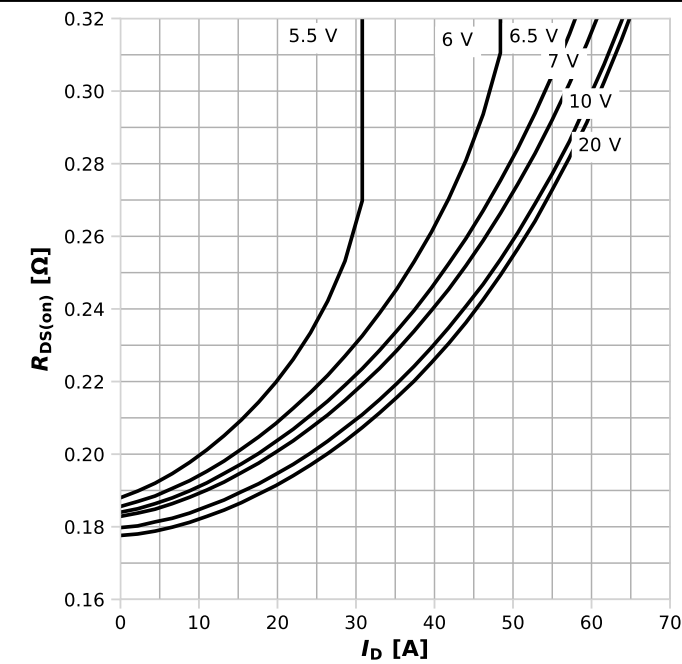
$I_D = f(V_{DS})$; $T_j = 25\text{ °C}$; parameter: V_{GS}

Diagram 6: Typ. output characteristics



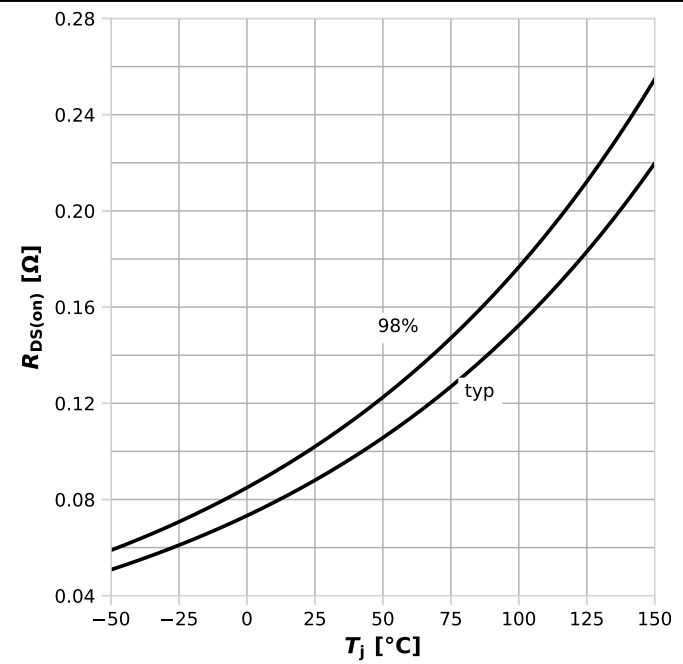
$I_D = f(V_{DS})$; $T_j = 125\text{ °C}$; parameter: V_{GS}

Diagram 7: Typ. drain-source on-state resistance



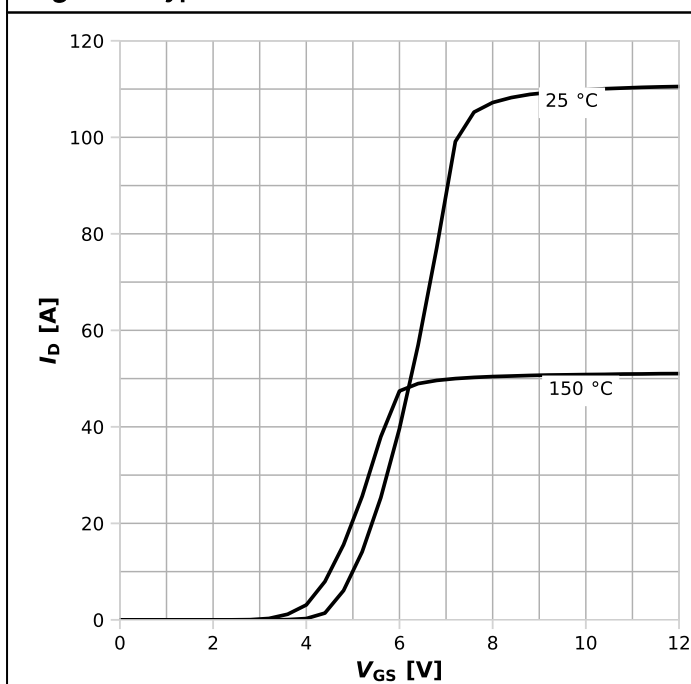
$R_{DS(on)} = f(I_D)$; $T_j = 125\text{ °C}$; parameter: V_{GS}

Diagram 8: Drain-source on-state resistance



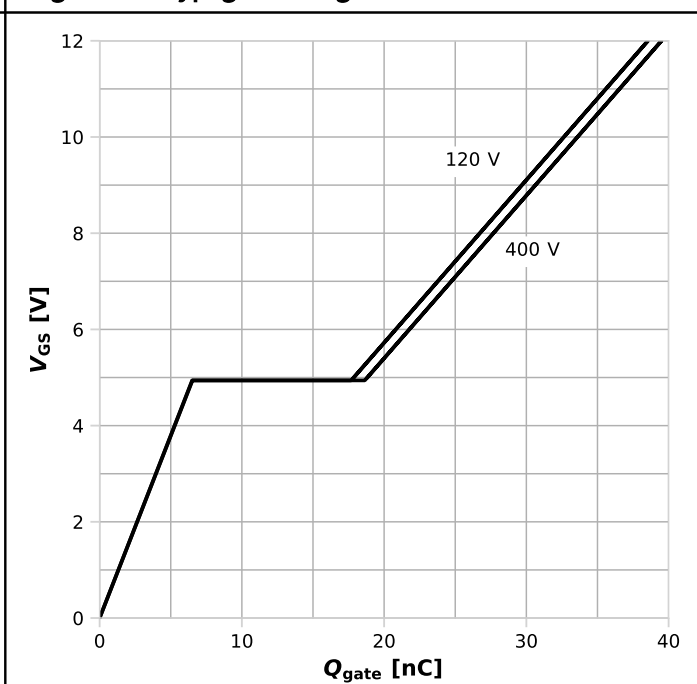
$R_{DS(on)} = f(T_j)$; $I_D = 7.8\text{ A}$; $V_{GS} = 10\text{ V}$

Diagram 9: Typ. transfer characteristics



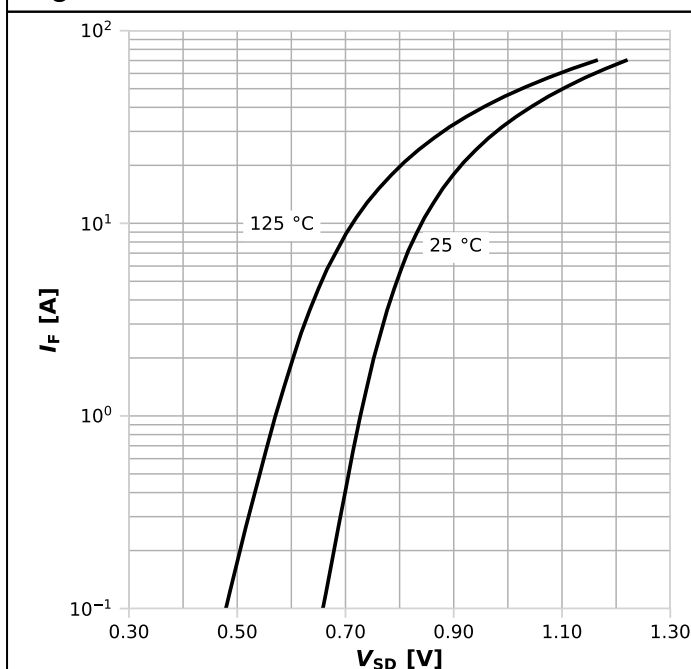
$I_D = f(V_{GS})$; $V_{DS} = 20V$; parameter: T_j

Diagram 10: Typ. gate charge



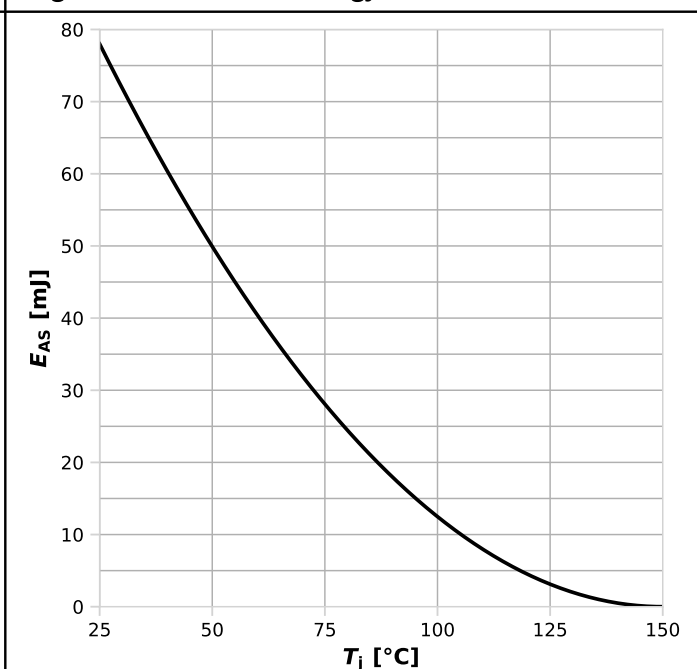
$V_{GS} = f(Q_{gate})$; $I_D = 7.8$ A pulsed; parameter: V_{DD}

Diagram 11: Forward characteristics of reverse diode



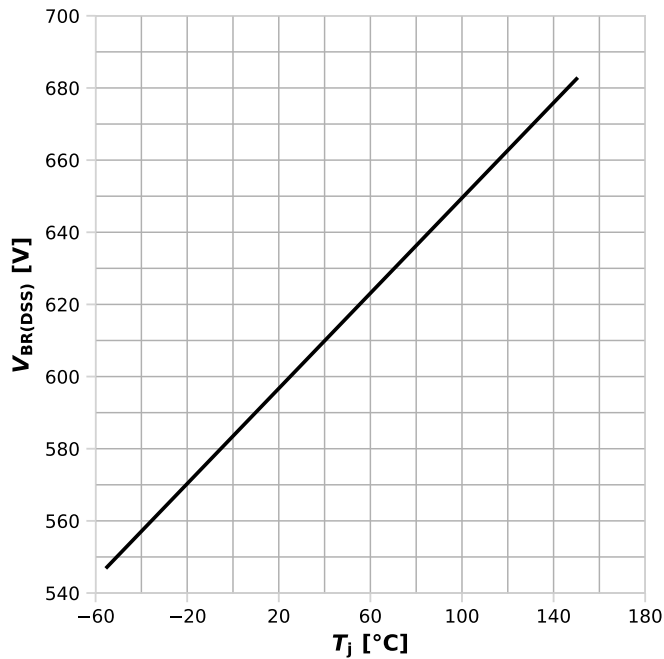
$I_F = f(V_{SD})$; parameter: T_j

Diagram 12: Avalanche energy



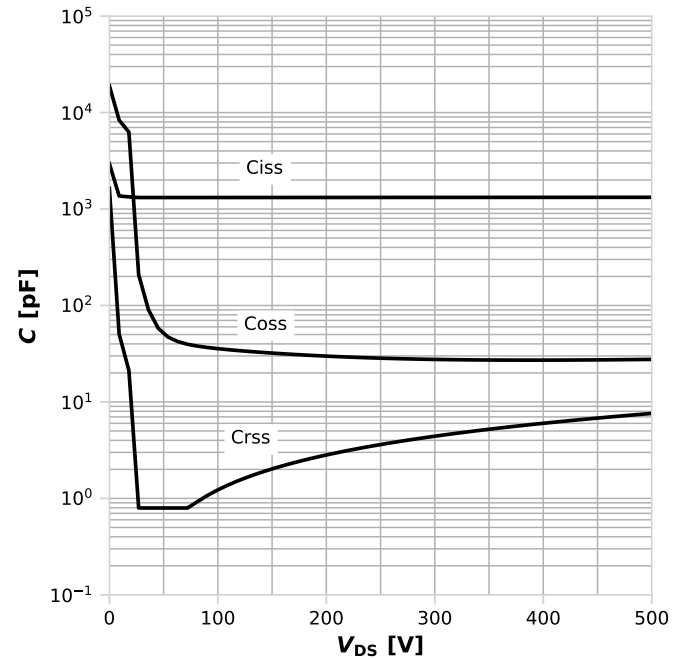
$E_{AS} = f(T_j)$; $I_D = 4.4$ A; $V_{DD} = 50$ V

Diagram 13: Drain-source breakdown voltage



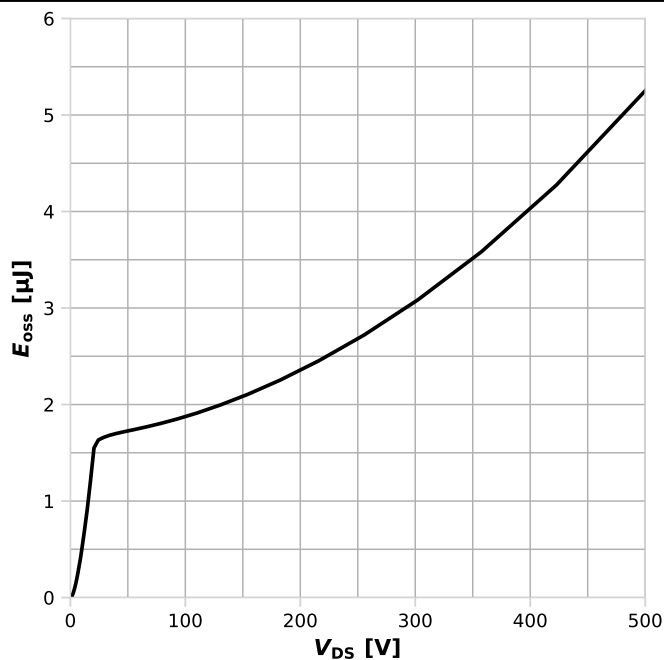
$$V_{BR(DSS)} = f(T_j); I_D = 1 \text{ mA}$$

Diagram 14: Typ. capacitances



$$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 250 \text{ kHz}$$

Diagram 15: Typ. Coss stored energy



$$E_{oss} = f(V_{DS})$$

5 Test circuits

Table 8 Diode characteristics

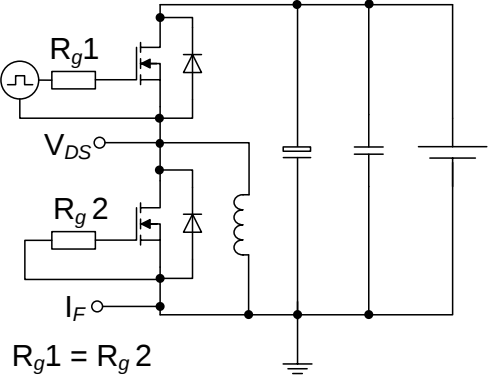
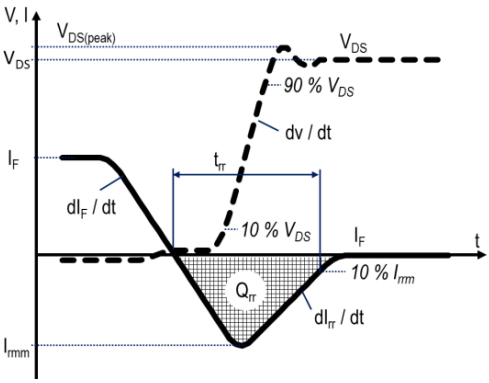
Test circuit for diode characteristics	Diode recovery waveform
 $R_{g1} = R_{g2}$	

Table 9 Switching times (ss)

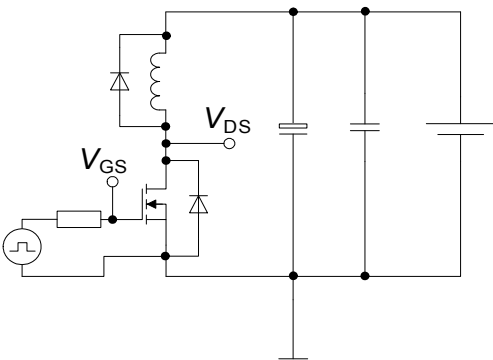
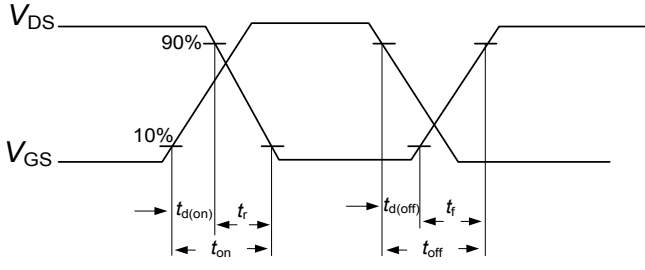
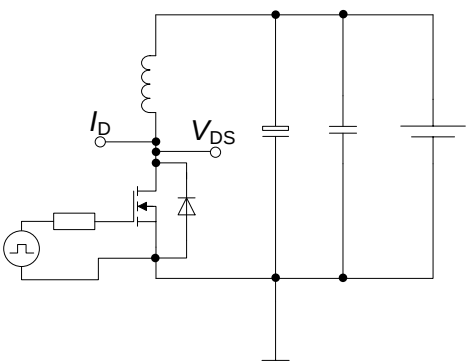
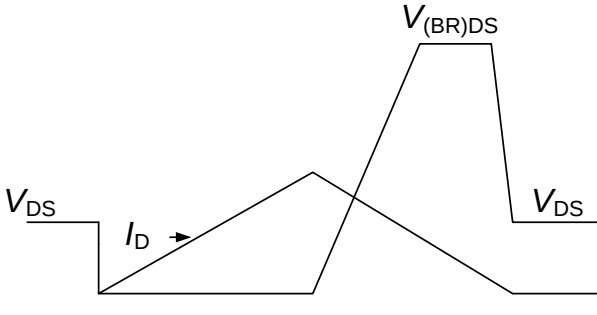
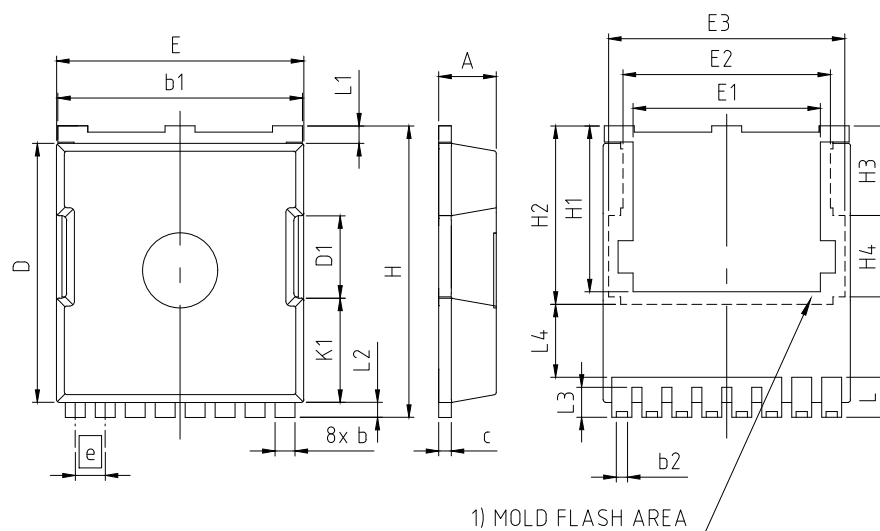
Switching times test circuit for inductive load	Switching times waveform
	

Table 10 Unclamped inductive load (ss)

Unclamped inductive load test circuit	Unclamped inductive waveform
	

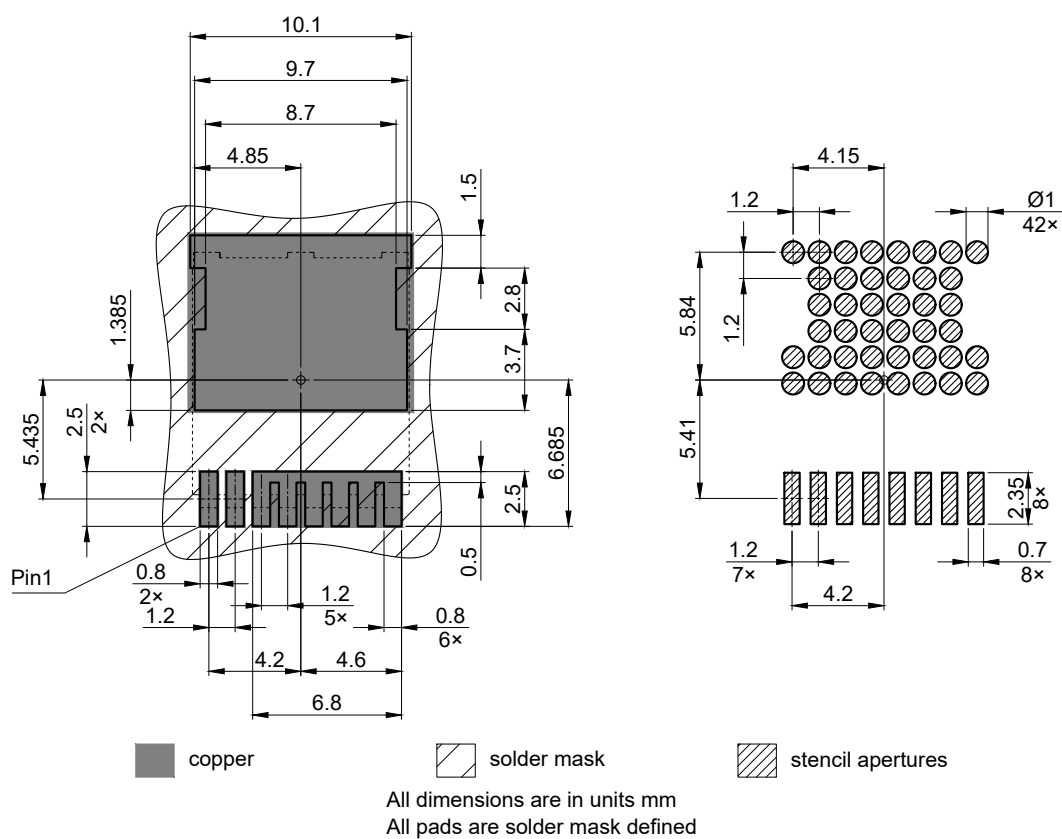
6 Package outlines

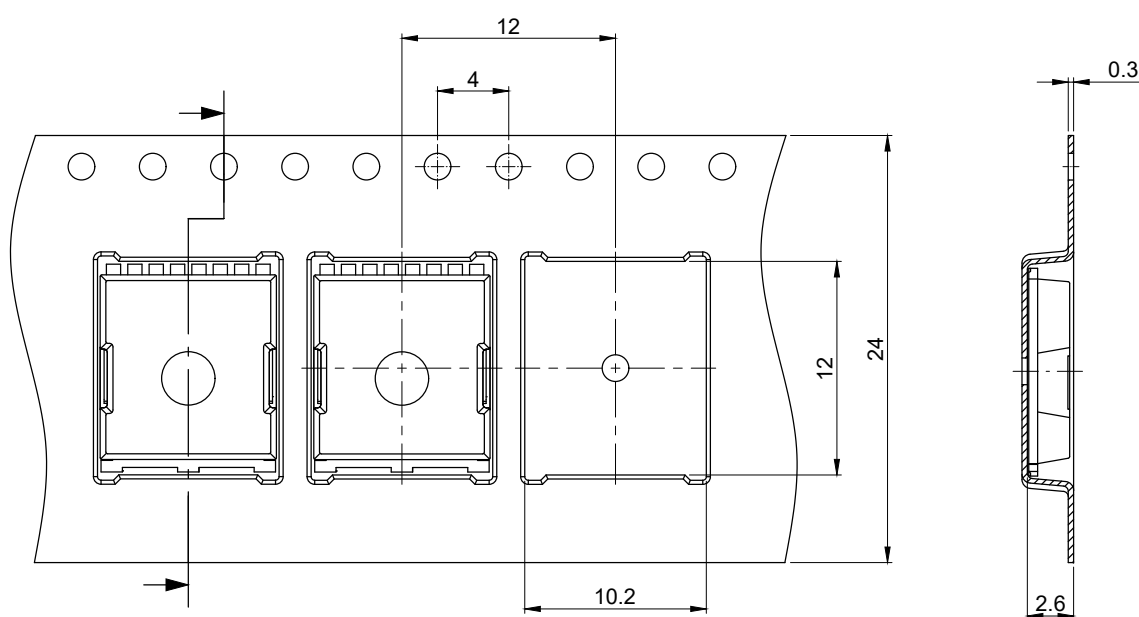


PACKAGE - GROUP NUMBER: PG-HSOF-8-U02		
DIMENSIONS	MILLIMETERS	
	MIN.	MAX.
A	2.20	2.40
b	0.70	0.90
b1	9.70	9.90
b2	0.42	0.50
c	0.40	0.60
D	10.28	10.58
D1	3.30	
E	9.70	10.10
E1	7.50	
E2	8.50	
E3	9.46	
e	1.20 (BSC)	
H	11.48	11.88
H1	6.55	6.95
H2	7.15	
H3	3.59	
H4	3.26	
N	8	
K1	4.18	
L	1.40	1.80
L1	0.50	0.90
L2	0.50	0.70
L3	1.00	1.30
L4	2.62	2.81

1) PARTIALLY COVERED WITH MOLD FLASH

Figure 1 Outline PG-HSOF-8, dimensions in mm


Figure 2 Footprint drawing PG-HSOF-8, dimensions in mm



All dimensions are in units mm

The drawing is in compliance with ISO 128-30, Projection Method 1 []

Figure 3 Packaging variant PG-HSOF-8, dimensions in mm

7 Appendix A

Table 11 **Related links**

- [IFX CoolMOS™ G7 Webpage](#)
- [IFX CoolMOS™ G7 application note](#)
- [IFX CoolMOS™ G7 simulation model](#)
- [IFX Design tools](#)

Revision history

IPT60R102G7

Revision 2025-02-03, Rev. 2.2

Previous revisions

Revision	Date	Subjects (major changes since last revision)
2.0	2016-12-15	Release of final version
2.1	2020-10-27	Content update diagram 2,3,4,7,8 and format update
2.2	2025-02-03	Implementation of standardized Infineon Umbrella-Templates for package drawings. H1 Extension from 6.75 to 6.95 MAX

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Published by

Infineon Technologies AG

81726 München, Germany

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